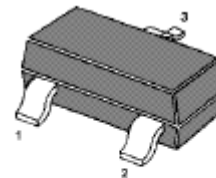


Kingtronics®**MMBTA10 THRU
MMBTA11****NPN Silicon Epitaxial Planar Transistor****VHF / UHF transistor**1. Base 2. Emitter 3. Collector
TO-236 Plastic Package**Absolute Maximum Ratings (T_a = 25°C)**

PARAMETER	SYMBOL	RATING	UNITS
Collector Base Voltage	V _{CBO}	30	V
Collector Emitter Voltage	V _{CEO}	25	V
Emitter Base Voltage	V _{EBO}	3	V
Collector Current	I _C	100	mA
Total Dissipation	P _{tot}	200	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	- 55 to + 150	°C

Characteristics at T_a = 25°C

PARAMETER	SYMBOL	MIN.	MAX.	UNITS	
DC Current Gain at V _{CE} = 10 V, I _C = 4 mA	h _{FE}	60	-	-	
Collector Base Breakdown Voltage at I _C = 100 μA	V _{(BR)CBO}	30	-	V	
Collector Emitter Breakdown Voltage at I _C = 1 mA	V _{(BR)CEO}	25	-	V	
Emitter Base Breakdown Voltage at I _E = 10 μA	V _{(BR)EBO}	3	-	V	
Collector Cutoff Current at V _{CB} = 25 V	I _{CBO}	-	100	nA	
Emitter Cutoff Current at V _{EB} = 2 V	I _{EBO}	-	100	nA	
Collector Emitter Saturation Voltage at I _C = 4 mA, I _B = 0.4 mA	V _{CE(sat)}	-	0.5	V	
Base-Emitter On Voltage at V _{CE} = 10 V, I _C = 4 mA	V _{BE(on)}	-	0.95	V	
Current Gain Bandwidth Product at V _{CE} = 10 V, I _C = 4 mA, f = 100 MHz	f _T	650	-	MHz	
Collector Base Capacitance at V _{CB} = 10 V, f = 1 MHz	C _{cb}	-	0.7	pF	
Collector Base Feedback Capacitance	MMBTA10	C _{rb}	0.35	0.65	pF
V _{CB} = 10 V, f = 1 MHz	MMBTA11	C _{rb}	0.6	0.9	pF

Note: Specifications are subject to change without notice

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